IN THE CLAIMS

Please amend claims 25 and 42 and add new claims 61-62 as follows.

Claims 26-41 and 43-60 are re-presented.

PENDING CLAIMS

25. (Amended Twice) A microelectronic structure comprising:

a substrate;

a gate electrode formed over the substrate; and

a source/drain terminal aligned with the gate electrode, the source/drain terminal comprising an implanted region in the substrate, a first silicide layer in the substrate, and a second silicide layer in the substrate,

wherein the first silicide layer and the second silicide layer are both in the implanted region in the substrate.

26. The microelectronic structure of claim 25, wherein the second silicide layer is thicker than the first silicide layer.

27. The microelectronic structure of claim 25, wherein the second silicide layer is spaced from the gate electrode.

28. The microelectronic structure of claim 25, comprising another source/drain terminal aligned with the gate electrode, the other source/drain terminal comprising an implanted region and two silicide layers.

29. The microelectronic structure of claim 25, wherein the first and second silicide layers comprise different metals.

30. The microelectronic structure of claim 25, wherein the first and second silicide layers comprise the same metal.

31. The microelectronic structure of claim 25, wherein the first silicide layer comprises $CoSi_2$.

32. The microelectronic structure of claim 25, wherein the first silicide layer comprises $TiSi_2$.

33. The microelectronic structure of claim 25, wherein the second silicide layer comprises nickel silicide.

34. The microelectronic structure of claim 25, wherein the second silicide layer comprises $CoSi_2$.

35. The microelectronic structure of claim 25, wherein the second silicide layer comprises $TiSi_2$.

36. The microelectronic structure of claim 25, comprising a silicidation barrier adjacent the gate electrode.

37. The microelectronic structure of claim 36, wherein the silicidation barrier comprises silicon nitride.

38. The microelectronic structure of claim 25, comprising a silicide layer adjacent the gate electrode.

39. The microelectronic structure of claim 38, wherein the silicide layer adjacent the gate electrode comprises nickel silicide.

40. The microelectronic structure of claim 38, wherein the silicide layer adjacent the gate electrode comprises $CoSi_2$.

41. The microelectronic structure of claim 38, wherein the silicide layer adjacent the gate electrode comprises $TiSi_2$.

42. (Amended Twice) A microelectronic structure comprising:

a substrate;

a gate electrode formed over the substrate; and

a source/drain terminal aligned with the gate electrode, the source/drain terminal comprising a first implanted region in the substrate, a first silicide layer in the substrate, a second implanted region in the substrate, and a second silicide layer in the substrate,

wherein the first silicide layer is in the first implanted region in the substrate and the second silicide layer is in the second implanted region in the substrate.

43. The microelectronic structure of claim 42, wherein the first silicide layer is contained within the first implanted region.

44. The microelectronic structure of claim 42, wherein the second silicide layer is thicker than the first implanted region.

45. The microelectronic structure of claim 42, wherein the second implanted region is thicker than the first implanted region.

46. The microelectronic structure of claim 42, wherein the second implanted region and the second silicide layer are spaced from the gate electrode.

47. The microelectronic structure of claim 42, comprising another source/drain terminal aligned with the gate electrode, the other source/drain terminal comprising two implanted regions and two silicide layers.

48. The microelectronic structure of claim 42, wherein the first and second silicide layers comprise different metals.

49. The microelectronic structure of claim 42, wherein the first and second silicide layers comprise the same metal.

50. The microelectronic structure of claim 42, wherein the first silicide layer comprises $CoSi_2$.

51. The microelectronic structure of claim 42, wherein the first silicide layer comprises $TiSi_2$.

52. The microelectronic structure of claim 42, wherein the second silicide layer comprises nickel silicide.

53. The microelectronic structure of claim 42, wherein the second silicide layer comprises $CoSi_2$.

54. The microelectronic structure of claim 42, wherein the second silicide layer comprises $TiSi_2$.

55. The microelectronic structure of claim 42, comprising a silicidation barrier adjacent the gate electrode.

56. The microelectronic structure of claim 55, wherein the silicidation barrier comprises silicon nitride.

57. The microelectronic structure of claim 42, comprising a silicide layer adjacent the gate electrode.

58. The microelectronic structure of claim 57, wherein the silicide layer adjacent the gate electrode comprises nickel silicide.

59. The microelectronic structure of claim 57, wherein the silicide layer adjacent the gate electrode comprises $CoSi_2$.

60. The microelectronic structure of claim 57, wherein the silicide layer adjacent the gate electrode comprises $TiSi_2$.

61. (New) The microelectronic structure of claim 25, wherein the substrate comprises silicon.

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62. (New) The microelectronic structure of claim 42, wherein the substrate comprises silicon.

add E'